

### 2SC2482 TRANSISTOR (NPN)

#### FEATURE

Power dissipation

$P_{CM}$ : 0.9 W ( $T_{amb}=25^{\circ}C$ )

Collector current

$I_{CM}$ : 0.1 A

Collector-base voltage

$V_{(BR)CBO}$ : 300 V

Operating and storage junction temperature range

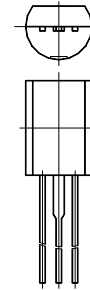
$T_J, T_{stg}$ :  $-55^{\circ}C$  to  $+150^{\circ}C$

#### TO-92MOD

1. EMITTER

2. COLLECTOR

3. BASE



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#### ELECTRICAL CHARACTERISTICS ( $T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu A, I_E=0$	300		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=3\text{ mA}, I_B=0$	300		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu A, I_C=0$	7		V
Collector cut-off current	$I_{CBO}$	$V_{CB}=240\text{ V}, I_E=0$		1	$\mu A$
Collector cut-off current	$I_{CEO}$	$V_{CB}=220\text{ V}, I_B=0$		5	$\mu A$
Emitter cut-off current	$I_{EBO}$	$V_{EB}=7\text{ V}, I_C=0$		1	$\mu A$
DC current gain	$h_{FE(1)}$	$V_{CE}=10\text{ V}, I_C=20\text{ mA}$	30	150	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=10\text{ mA}, I_B=1\text{ mA}$		1	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=10\text{ mA}, I_B=1\text{ mA}$		1	V
Transition frequency	$f_T$	$V_{CE}=10\text{ V}, I_C=20\text{ mA}$ $f=30\text{ MHz}$	50		MHz

#### CLASSIFICATION OF $h_{FE(1)}$

Rank	O	Y
Range	30-90	90-150